CHAPTER - 45
SEMICONDUCTOR AND SEMICONDUCTOR DEVICES

1. $f = 1013\ kg/m^3$, $V = 1\ m^3$
   $m = fV = 1013 \times 1 = 1013$ kg
   No.of atoms = $\frac{1013 \times 10^3 \times 6 \times 10^{23}}{23}$ = 264.26×10^{26}.
   a) Total no.of states = 2 N = $2 \times 264.26 \times 10^{26}$ = $528.52 = 5.3 \times 10^{28} \times 10^{26}$
   b) Total no.of unoccupied states = 2.65×10^{26}.
2. In a pure semiconductor, the no.of conduction electrons = no.of holes
   Given volume = 1 cm × 1 cm × 1 mm
   $= 1 \times 10^{-2} \times 1 \times 10^{-2} \times 1 \times 10^{-3} = 10^{-7}\ m^3$
   No.of electrons = $6 \times 10^{19} \times 10^{-7} = 6 \times 10^{12}$.
   Hence no.of holes = 6×10^{12}.
3. $E = 0.23$ eV, $K = 1.38 \times 10^{-23}$
   KT = E
   $\Rightarrow 1.38 \times 10^{-23} \times T = 0.23 \times 1.6 \times 10^{-19}$
   $\Rightarrow T = \frac{0.23 \times 1.6 \times 10^{-19}}{1.38 \times 10^{-23}} = \frac{0.23 \times 1.6 \times 10^{4}}{1.38}$ = $0.2676 \times 10^4 = 2670$.
4. Bandgap = 1.1 eV, T = 300 K
   a) Ratio = $\frac{1.1}{KT} = \frac{1.1}{8.62 \times 10^{-5} \times 3 \times 10^2}$ = 42.53= 43
   b) 4.253′ = $\frac{1.1}{8.62 \times 10^{-5} \times T}$ or T = $\frac{1.1 \times 10^5}{4.253 \times 8.62}$ = 3000.47 K.
5. 2KT = Energy gap between acceptor band and valency band
   $\Rightarrow 2 \times 1.38 \times 10^{-23} \times 300$
   $\Rightarrow E = (2 \times 1.38 \times 3) \times 10^{-21}\ J = \frac{6 \times 1.38}{1.6} \times \frac{10^{-21}}{10^{-19}} eV = \left(\frac{6 \times 1.38}{1.6}\right) \times 10^{-2} eV$
   $= 5.175 \times 10^{-2}$ eV = 51.75 meV = 50 meV.
6. Given :
   Band gap = 3.2 eV,
   $E = hc / \lambda = 1242 / \lambda = 3.2$ or $\lambda = 388.1$ nm.
7. $\lambda = 820$ nm
   $E = hc / \lambda = 1242/820 = 1.5$ eV
8. Band Gap = 0.65 eV, λ =?
   $E = hc / \lambda = 1242 / 0.65 = 1910.7 \times 10^{-9}\ m = 1.9 \times 10^{-5}$ m.
9. Band gap = Energy need to over come the gap
   $\frac{hc}{\lambda} = \frac{1242 eV - nm}{620 nm}$ = 2.0 eV.
10. Given $n = e^{-\Delta E / 2KT}$, ΔE = Diamon → 6 eV ; ΔE Si → 1.1 eV
    Now, $n_1 = e^{-\Delta E_1 / 2KT} = e^{\frac{-6}{2 \times 300 \times 8.62 \times 10^{-5}}}$
    $n_2 = e^{-\Delta E_2 / 2KT} = e^{\frac{-1.1}{2 \times 300 \times 8.62 \times 10^{-5}}}$
    $\frac{n_1}{n_2} = \frac{4.14772 \times 10^{-51}}{5.7978 \times 10^{-10}}$ = 7.15×10^{-42}.
    Due to more ΔE, the conduction electrons per cubic metre in diamond is almost zero.

11. $\sigma = T^{3/2}\ e^{-\Delta E/2KT}$ at 4°K

$\sigma = 4^{3/2} = e^{\frac{-0.74}{2\times8.62\times10^{-5}\times4}} = 8 \times e^{-1073.08}$.

At 300 K,

$\sigma = 300^{3/2} e^{\frac{-0.67}{2\times8.62\times10^{-5}\times300}} = \frac{3\times1730}{8} e^{-12.95}$.

Ratio = $\frac{8\times e^{-1073.08}}{[(3\times1730)/8]\times e^{-12.95}} = \frac{64}{3\times1730} e^{-1060.13}$.

12. Total no.of charge carriers initially = $2 \times 7 \times 10^{15} = 14 \times 10^{15}$/Cubic meter

Finally the total no.of charge carriers = 14×10^{17} / m^3

We know :

The product of the concentrations of holes and conduction electrons remains, almost the same.

Let x be the no.of holes.

So, $(7 \times 10^{15}) \times (7 \times 10^{15}) = x \times (14 \times 10^{17} - x)$

$\Rightarrow 14x \times 10^{17} - x^2 = 79 \times 10^{30}$

$\Rightarrow x^2 - 14x \times 10^{17} - 49 \times 10^{30} = 0$

x = $\frac{14\times10^{17} \pm 14^2 \times \sqrt{10^{34} + 4\times49\times10^{30}}}{2}$ = 14.00035×10^{17}.

= Increased in no.of holes or the no.of atoms of Boron added.

$\Rightarrow$ 1 atom of Boron is added per $\frac{5\times10^{28}}{1386.035\times10^{15}} = 3.607 \times 10^{-3} \times 10^{13} = 3.607 \times 10^{10}$.

13. (No. of holes) (No.of conduction electrons) = constant.

At first :

No. of conduction electrons = 6×10^{19}

No.of holes = 6×10^{19}

After doping

No.of conduction electrons = 2×10^{23}

No. of holes = x.

$(6 \times 10^{19})\ (6 \times 10^{19}) = (2 \times 10^{23})x$

$\Rightarrow \frac{6\times6\times10^{19+19}}{2\times10^{23}} = x$

$\Rightarrow x = 18 \times 10^{15} = 1.8 \times 10^{16}$.

14. $\sigma = \sigma_0 e^{-\Delta E/2KT}$

$\Delta E = 0.650$ eV, T = 300 K

According to question, $K = 8.62 \times 10^{-5}$ eV

$\sigma_0 e^{-\Delta E/2KT} = 2 \times \sigma_0 e^{\frac{-\Delta E}{2\times K\times300}}$

$\Rightarrow e^{\frac{-0.65}{2\times8.62\times10^{-5}\times T}} = 6.96561 \times 10^{-5}$

Taking in on both sides,

We get, $\frac{-0.65}{2\times8.62\times10^{-5}\times T'} = -11.874525$

$\Rightarrow \frac{1}{T'} = \frac{11.574525\times2\times8.62\times10^{-5}}{0.65}$

$\Rightarrow$ T' = 317.51178 = 318 K.

15. Given band gap = 1 eV
    Net band gap after doping = $(1 - 10^{-3})$eV = 0.999 eV
    According to the question, $KT_1 = 0.999/50$
    $\Rightarrow T_1 = 231.78 = 231.8$
    For the maximum limit $KT_2 = 2 \times 0.999$
    $$\Rightarrow T_2 = \frac{2 \times 1 \times 10^{-3}}{8.62 \times 10^{-5}} = \frac{2}{8.62} \times 10^2 = 23.2.$$
    Temperature range is (23.2 – 231.8).
16. Depletion region 'd' = 400 nm = 4×10^{-7} m
    Electric field $E = 5 \times 10^5$ V/m
    a) Potential barrier $V = E \times d = 0.2$ V
    b) Kinetic energy required = Potential barrier $\times$ e = 0.2 eV [Where e = Charge of electron]
17. Potential barrier = 0.2 Volt
    a) K.E. = (Potential difference) $\times$ e = 0.2 eV (in unbiased cond^n)
    b) In forward biasing
       KE + Ve = 0.2e
       $\Rightarrow$ KE = 0.2e – 0.1e = 0.1e.
    c) In reverse biasing
       KE – Ve = 0.2 e
       $\Rightarrow$ KE = 0.2e + 0.1e = 0.3e.
18. Potential barrier 'd' = 250 meV
    Initial KE of hole = 300 meV
    We know : KE of the hole decreases when the junction is forward biased and increases when reverse blased in the given 'Pn' diode.
    So,
    a) Final KE = (300 – 250) meV = 50 meV
    b) Initial KE = (300 + 250) meV = 550 meV
19. $i_1 = 25\ \mu A$, $V = 200$ mV, $i_2 = 75\ \mu A$
    a) When in unbiased condition drift current = diffusion current
       $\therefore$ Diffusion current = 25 μA.
    b) On reverse biasing the diffusion current becomes 'O'.
    c) On forward biasing the actual current be x.
       x – Drift current = Forward biasing current
       $\Rightarrow x - 25\ \mu A = 75\ \mu A$
       $\Rightarrow x = (75 + 25)\ \mu A = 100\ \mu A$.
20. Drift current = 20 μA = 20×10^{-6} A.
    Both holes and electrons are moving
    $$\text{So, no.of electrons} = \frac{20 \times 10^{-6}}{2 \times 1.6 \times 10^{-19}} = 6.25 \times 10^{13}.$$
21. a) $e^{aV/KT} = 100$
    $$\Rightarrow e^{\frac{V}{8.62 \times 10^{-5} \times 300}} = 100$$
    $$\Rightarrow \frac{V}{8.62 \times 10^{-5} \times 300} = 4.605 \Rightarrow V = 4.605 \times 8.62 \times 3 \times 10^{-3} = 119.08 \times 10^{-3}$$
    $$R = \frac{V}{I} = \frac{V}{I_0(e^{ev/KT-1})} = \frac{119.08 \times 10^{-3}}{10 \times 10^{-6} \times (100-1)} = \frac{119.08 \times 10^{-3}}{99 \times 10^{-5}} = 1.2 \times 10^2.$$
    $V_0 = I_0 R$
    $\Rightarrow 10 \times 10^{-6} \times 1.2 \times 10^2 = 1.2 \times 10^{-3} = 0.0012$ V.

c) $0.2 = \frac{KT}{ei_0} e^{-eV/KT}$

$K = 8.62 \times 10^{-5}$ eV/K, T = 300 K

$i_0 = 10 \times 10^{-5}$ A.

Substituting the values in the equation and solving

We get V = 0.25

22. a) $i_0 = 20 \times 10^{-6}$A, T = 300 K, V = 300 mV

$i = i_0 e^{\frac{ev}{KT} - 1} = 20 \times 10^{-6}(e^{\frac{100}{8.62}} - 1) = 2.18$ A = 2 A.

b) $4 = 20 \times 10^{-6}(e^{\frac{V}{8.62 \times 3 \times 10^{-2}}} - 1) \Rightarrow e^{\frac{V \times 10^3}{8.62 \times 3}} - 1 = \frac{4 \times 10^6}{20}$

$\Rightarrow e^{\frac{V \times 10^3}{8.62 \times 3}} = 200001 \Rightarrow \frac{V \times 10^3}{8.62 \times 3} = 12.2060$

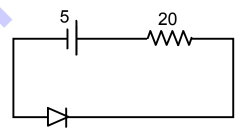
$\Rightarrow$ V = 315 mV = 318 mV.

23. a) Current in the circuit = Drift current

(Since, the diode is reverse biased = 20 μA)

b) Voltage across the diode = $5 - (20 \times 20 \times 10^{-6})$

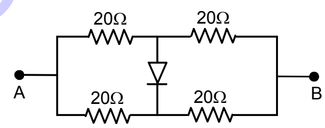
$= 5 - (4 \times 10^{-4}) = 5$ V.



24. From the figure :

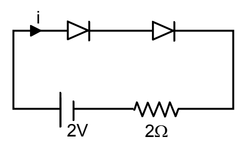
According to wheat stone bridge principle, there is no current through the diode.

Hence net resistance of the circuit is $\frac{40}{2} = 20\ \Omega$.



25. a) Since both the diodes are forward biased net resistance = 0

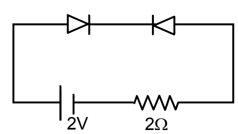
$i = \frac{2V}{2\Omega} = 1$ A



b) One of the diodes is forward biased and other is reverse biase.

Thus the resistance of one becomes ∞.

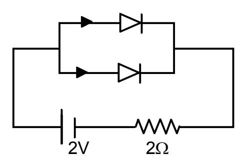
$i = \frac{2}{2 + \infty} = 0$ A.



Both are forward biased.

Thus the resistance is 0.

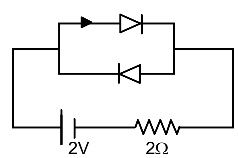
$i = \frac{2}{2} = 1$ A.



One is forward biased and other is reverse biased.

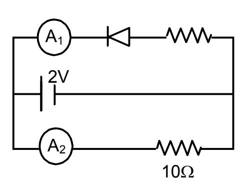
Thus the current passes through the forward biased diode.

$\therefore i = \frac{2}{2} = 1$ A.

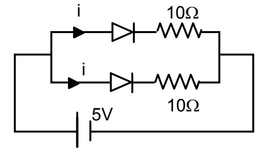


26. The diode is reverse biased. Hence the resistance is infinite. So, current through A_1 is zero.

For A_2, current $= \frac{2}{10} = 0.2$ Amp.

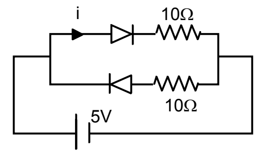


27. Both diodes are forward biased. Thus the net diode resistance is 0.



$$i = \frac{5}{(10+10)/10.10} = \frac{5}{5} = 1 \text{ A.}$$

One diode is forward biased and other is reverse biased.



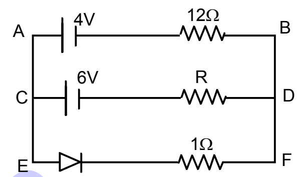
Current passes through the forward biased diode only.

$$i = \frac{V}{R_{net}} = \frac{5}{10+0} = 1/2 = 0.5 \text{ A.}$$

28. a) When R = 12 Ω

The wire EF becomes ineffective due to the net (–)ve voltage.

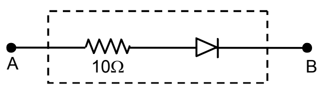
Hence, current through R = 10/24 = 0.4166 = 0.42 A.

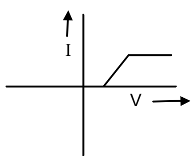


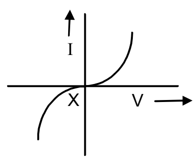
b) Similarly for R = 48 Ω.

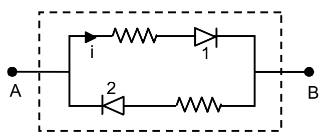
$$i = \frac{10}{(48+12)} = 10/60 = 0.16 \text{ A.}$$

29.

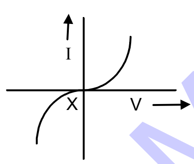


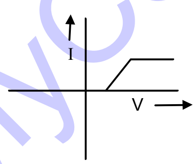




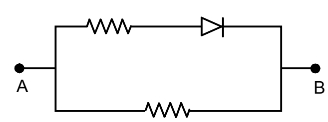


Since the diode 2 is reverse biased no current will pass through it.





30. Let the potentials at A and B be V_A and V_B respectively.



i) If $V_A > V_B$

Then current flows from A to B and the diode is in forward biased.

Eq. Resistance = 10/2 = 5 Ω.

ii) If $V_A < V_B$

Then current flows from B to A and the diode is reverse biased.

Hence Eq.Resistance = 10 Ω.

31. δI_b = 80 μA – 30 μA = 50 μA = 50×10^{-6} A

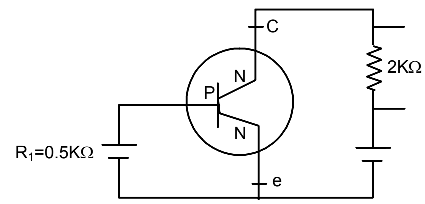
δI_c = 3.5 mA – 1 mA = –2.5 mA = 2.5×10^{-3} A

$$\beta = \left(\frac{\delta I_c}{\delta I_b}\right) V_{ce} = \text{constant}$$

$$\Rightarrow \frac{2.5 \times 10^{-3}}{50 \times 10^{-6}} = \frac{2500}{50} = 50.$$

Current gain = 50.

32. $\beta = 50$, $\delta I_b = 50\ \mu A$,
$V_0 = \beta \times RG = 50 \times 2/0.5 = 200$.



a) $VG = V_0/V_1 = \frac{V_0}{V_i} = \frac{V_0}{\delta I_b \times R_i} = \frac{200}{50 \times 10^{-6} \times 5 \times 10^2}$ = 8000 V.

b) $\delta V_i = \delta I_b \times R_i = 50 \times 10^{-6} \times 5 \times 10^2 = 0.00025$ V = 25 mV.

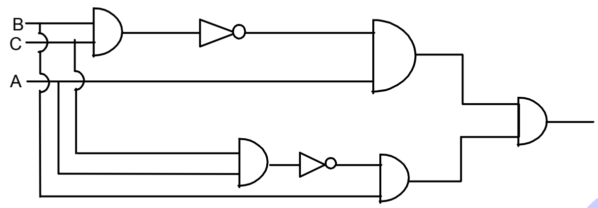
c) Power gain = $\beta^2 \times RG = \beta^2 \times \frac{R_0}{R_i} = 2500 \times \frac{2}{0.5} = 10^4$.

33. X = $A\overline{BC} + B\overline{CA} + C\overline{AB}$

a) A = 1, B = 0, C = 1
X = 1.

b) A = B = C = 1
X = 0.

34. For $A\overline{BC} + B\overline{CA}$



35. LHS = $AB \times \overline{AB}$ = $X + \overline{X}$ [X = AB]

If X = 0, $\overline{X}$ = 1

If $\overline{X}$ = 0, X = 1

$\Rightarrow$ 1 + 0 or 0 + 1 = 1

$\Rightarrow$ RHS = 1 (Proved)

♠ ♠ ♠`